

Comparative study of ion beam-irradiation effects on silica and α -quartz: Evidences for excitonic mechanisms

J. Manzano-Santamaría^{a)}, J. Olivares,^(a,b) O. Peña-Rodríguez^(c), A. Rivera^(c) M.L. Crespillo^(a,b) and F. Agulló-López^(a)

^(a) Centro de Microanálisis de Materiales, Universidad Autónoma de Madrid, Faraday 3, E-28049, Madrid, Spain

^(b) Instituto de Óptica, Consejo Superior de Investigaciones Científicas, Serrano 121, E-28016, Madrid, Spain

^(c) Instituto de Fusión Nuclear, Universidad Politécnica de Madrid, José Gutiérrez Abascal 2, E-28006, Madrid, Spain

Introduction

- SiO₂

- Simple composition and structure; Crystalline and amorphous phases
- Adequate for atomistic simulations
- Abundant in nature. Relevant for many technologies

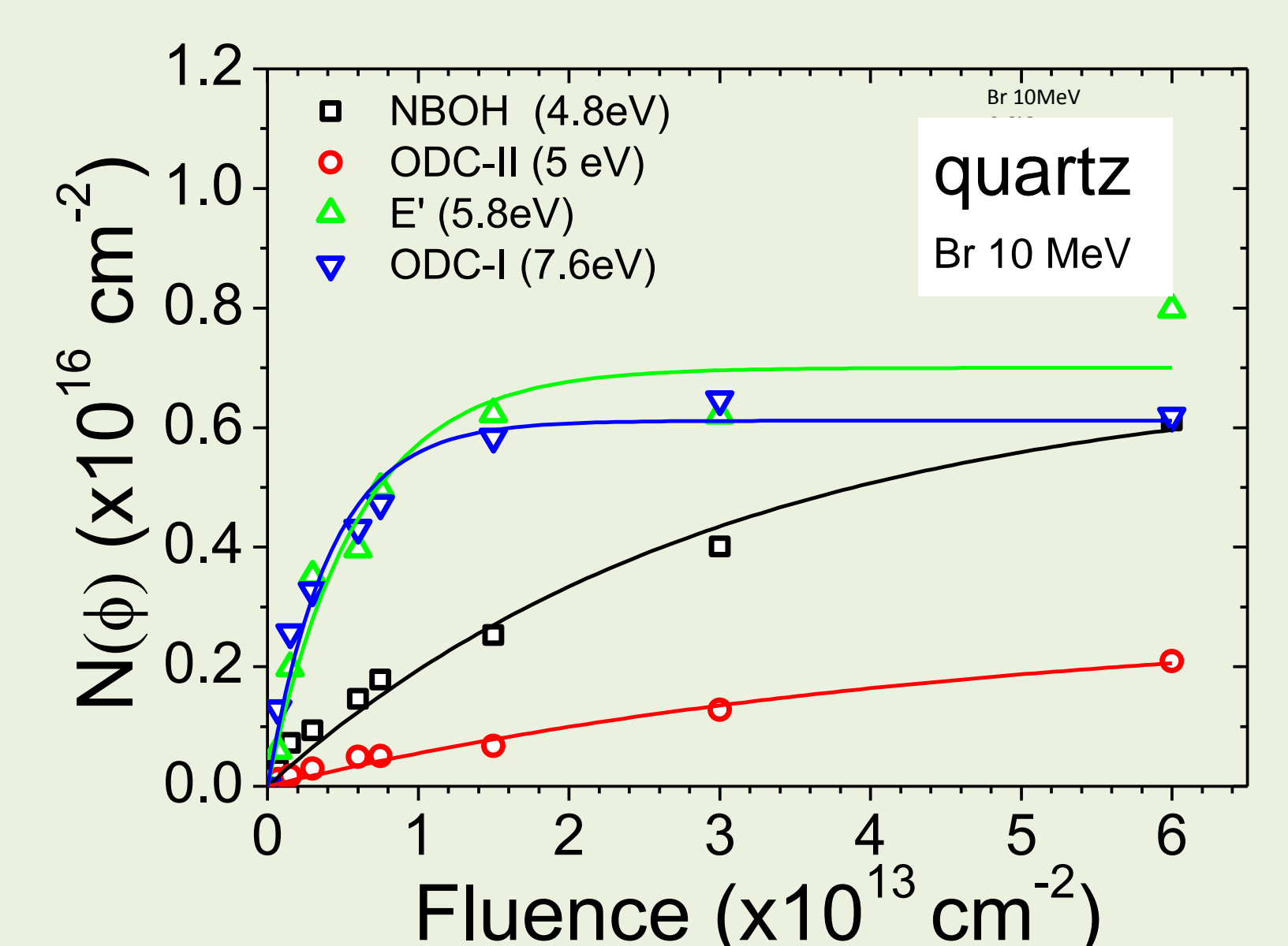
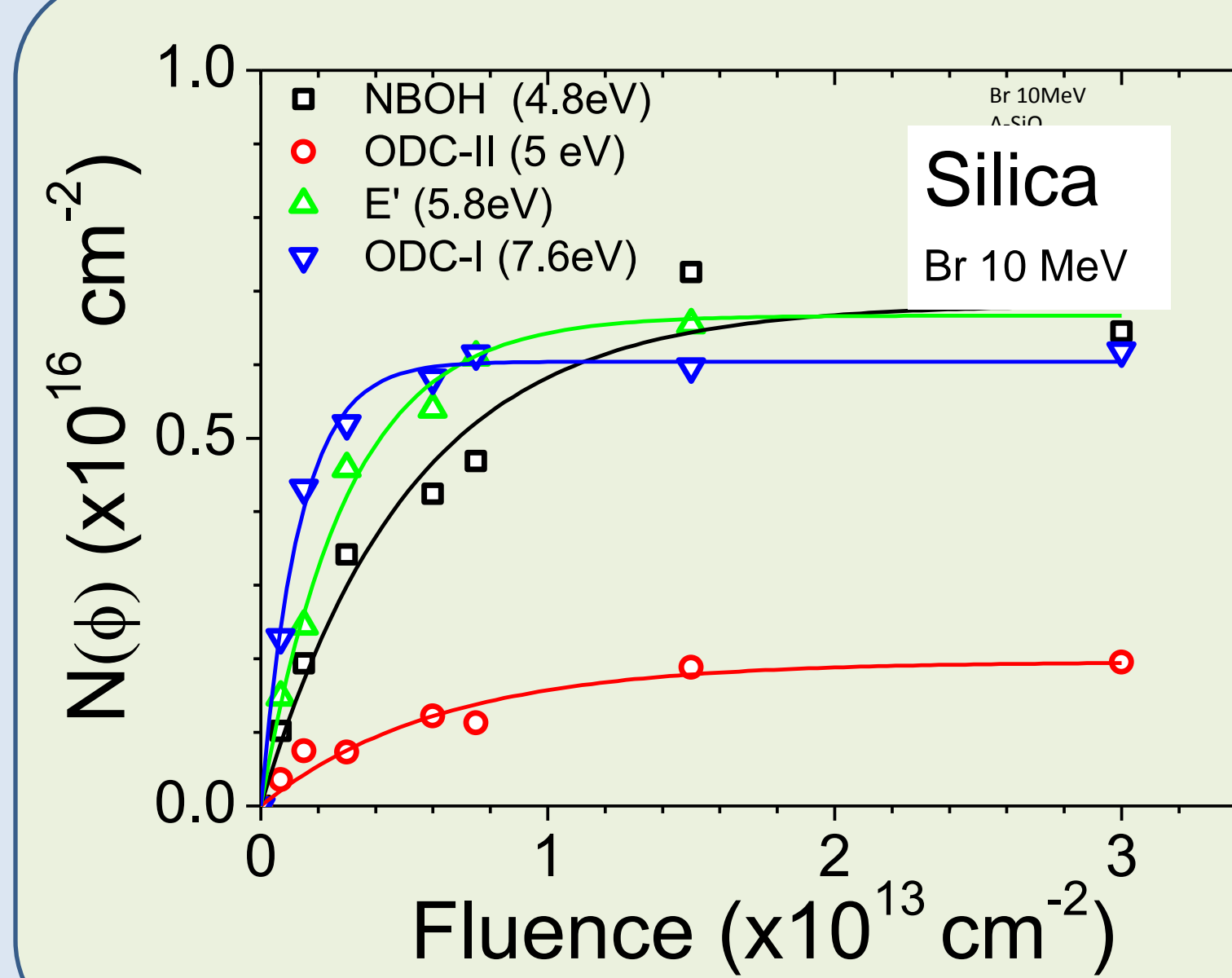
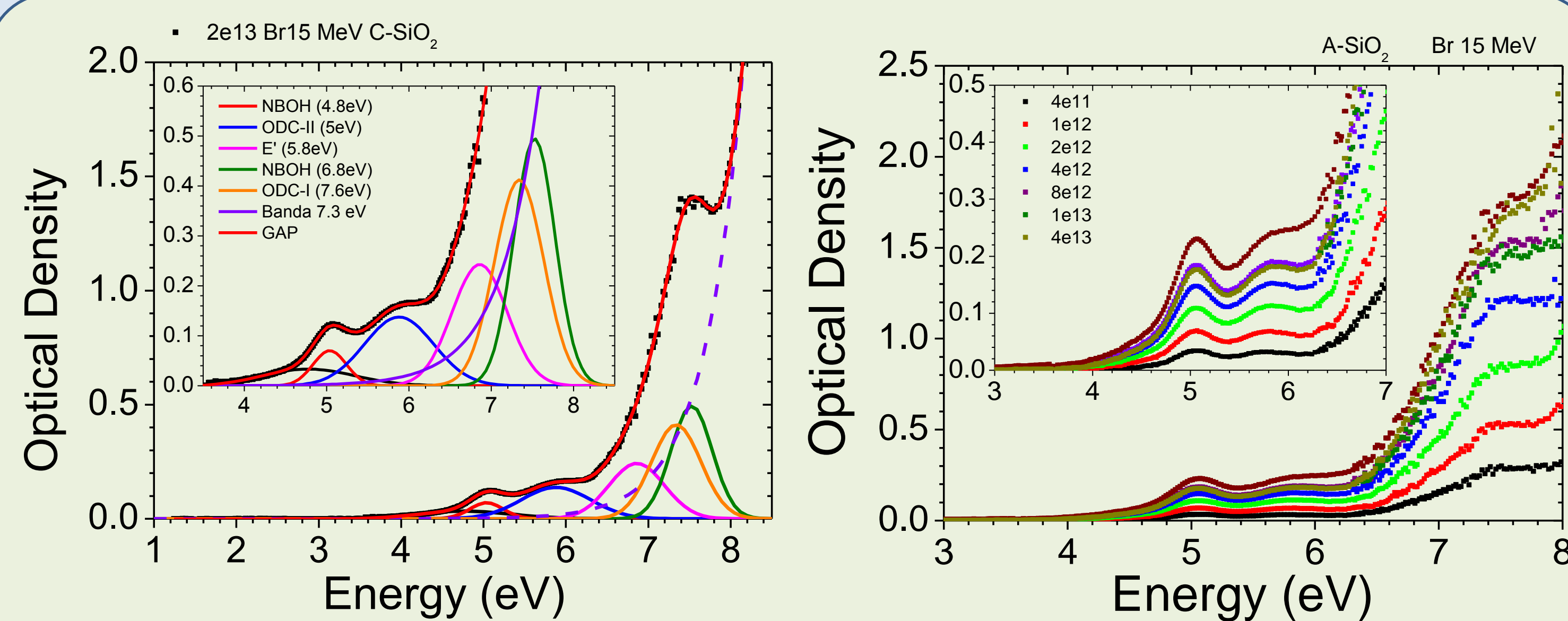
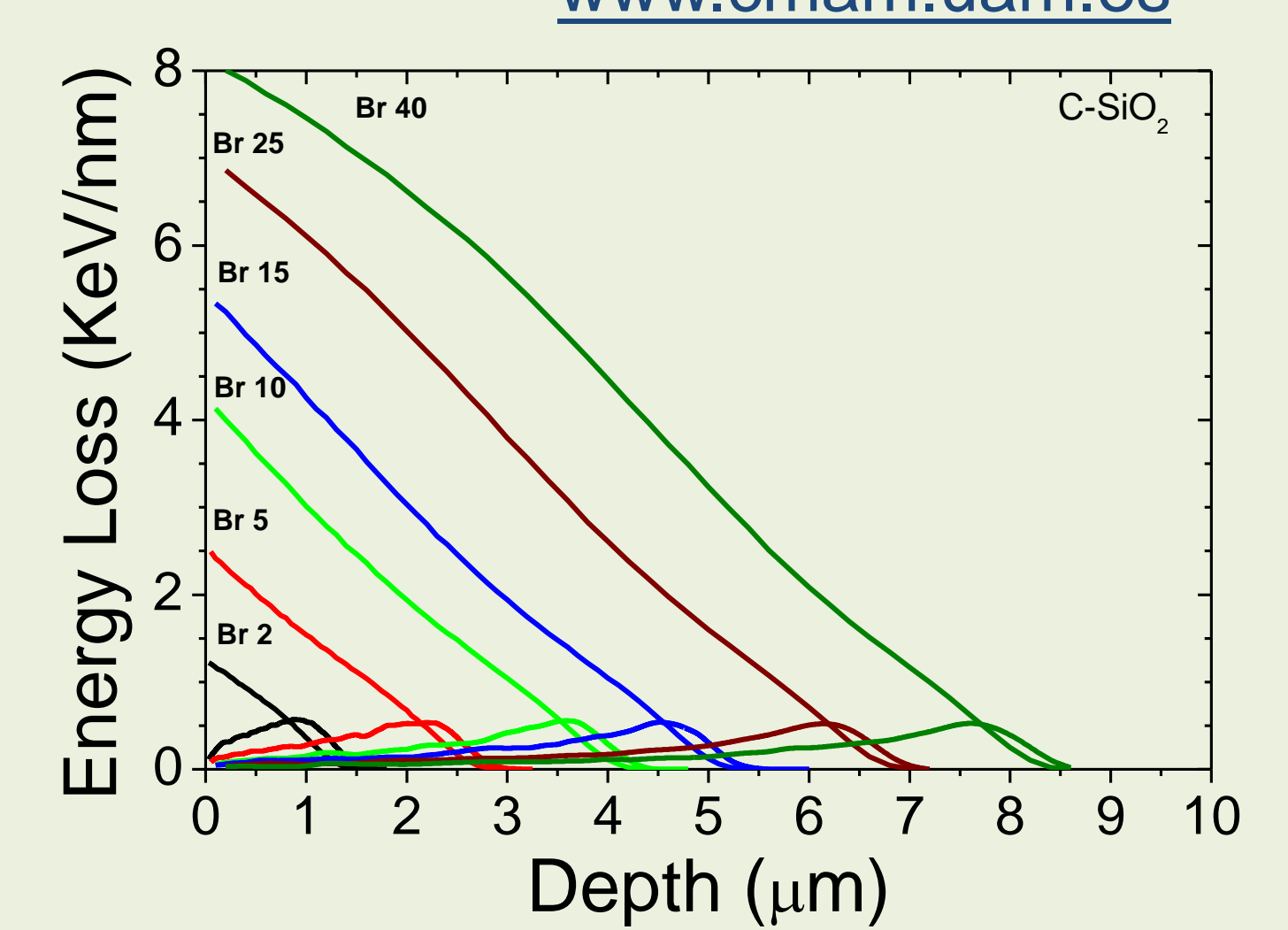
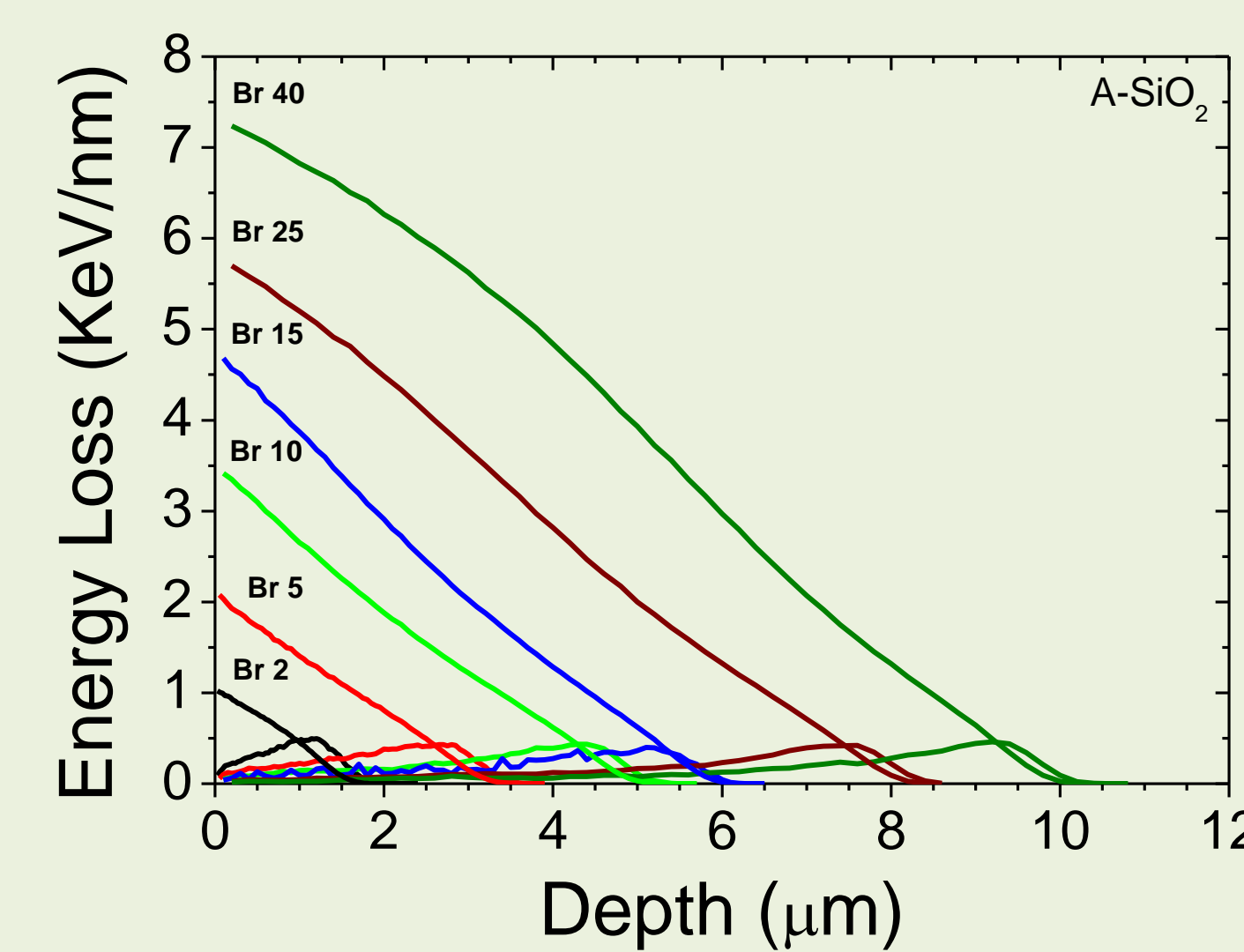
- Irradiation with swift heavy ions:

- They provide EXTREME physical conditions
- Very high excitation densities similar to high power lasers
- Very high local temperatures
- By playing with high energy and heavy mass (SHI) :
- One can go from low electronic excitations (collisions regime) to high electronic excitations (electronic regime)

Experimental

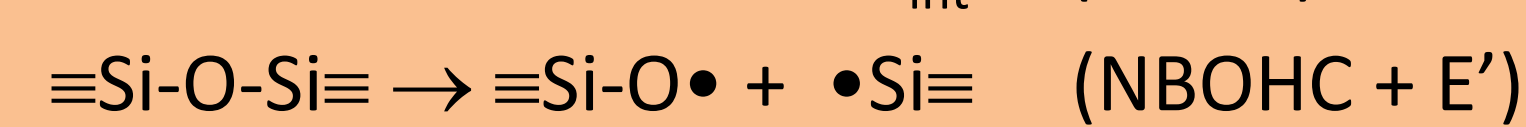
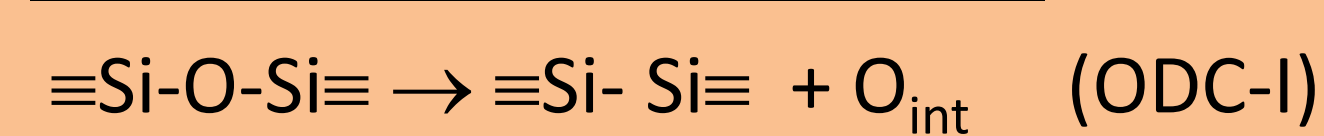
- Samples: SiO₂ 6x6x1 mm³ • Ions: Br 2-40 MeV • J \approx 10-30 nA
- Beam inhomogeneity < 10 %

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Position (eV)	FWHM (eV)	Oscillator strength	Defect
4.8	1 - 1.2	0.05	NBOHC
5.0	0.35 - 0.4	0.15	ODC-II
5.8	0.8 - 0.9	0.15	E'
6.8	1.7	0.05	NBOHC
7.6	0.5	0.4	ODC-I

Excitonic mechanism



Ref [4,5]

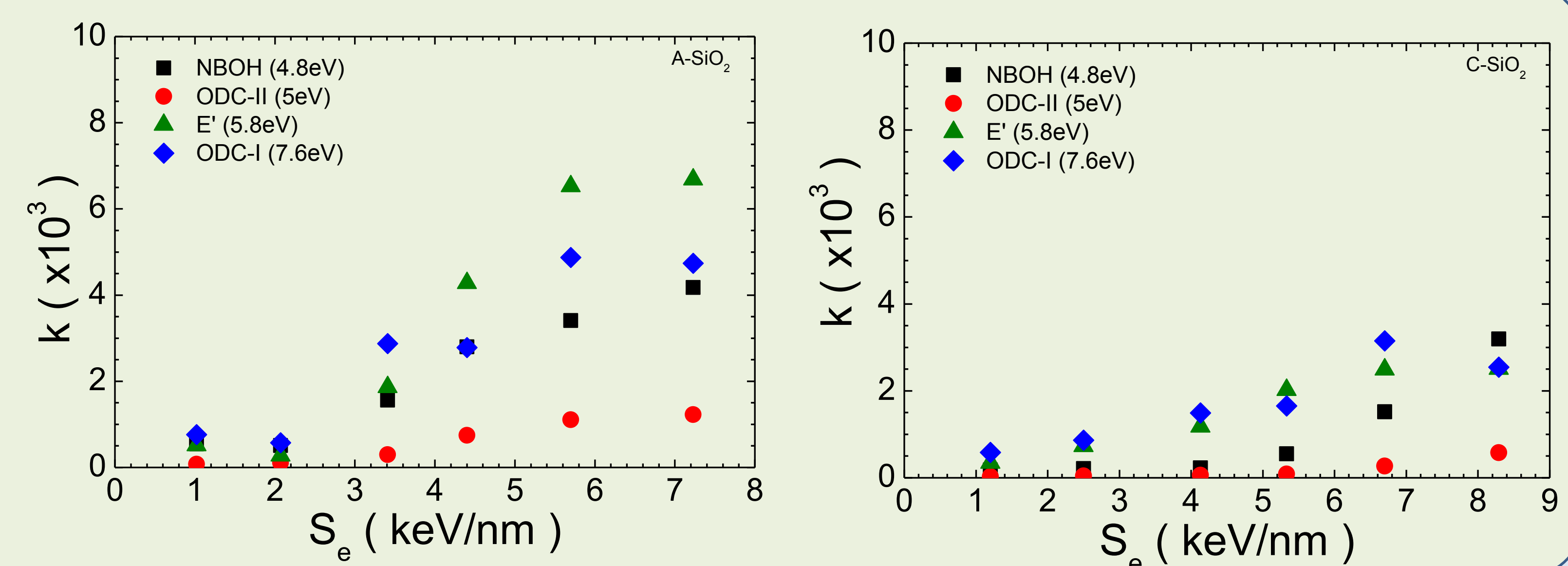
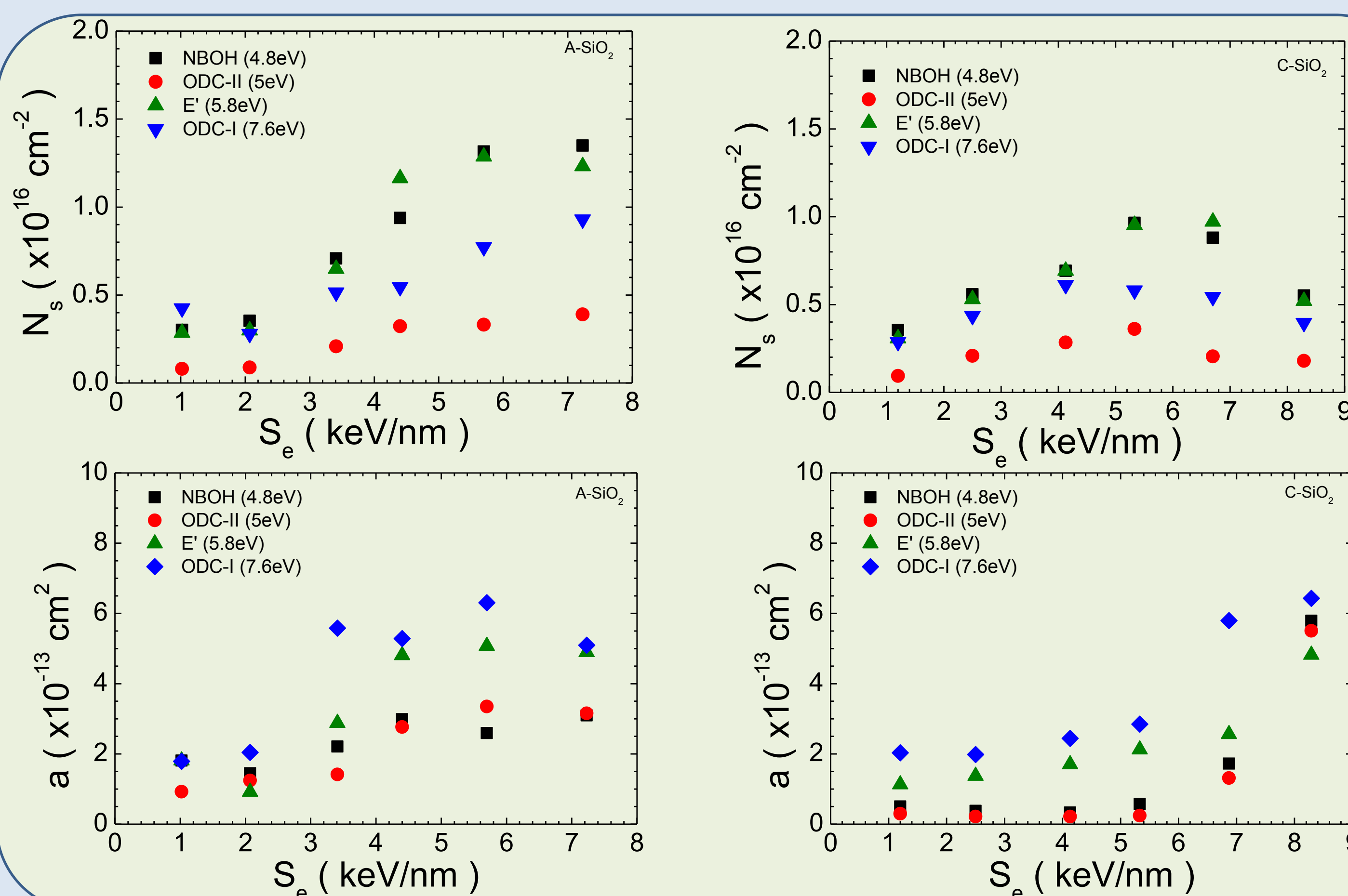
Excitons self trap preferentially in stressed bonds

Ref [6,7]

- Growth curves: Poisson-like. Cross-sections σ and saturation values N_s .
- Why the growth reaches a steady state?
 - Saturation or dynamical equilibrium between creation and annealing?
- Dependence of k and N_s on stopping power S_e

$$N(\phi) = N_s \{1 - \exp(-\sigma\phi)\}$$

$$k = \sigma N_s$$



Conclusions

- Creation rates show a rather linear dependence on ion energy except at low enough energies where a constant stage is observed
- Higher efficiency for defect creation in silica (role of strained bonds?)
- N_s grows with ion energy up to a maximum value and from then onwards it either saturates (silica) or decreases (quartz). This effect implies an annihilation term.
- Growth kinetics suggest that excitonic mechanisms (probably in synergy with thermal ones) play an important role in defect formation.

References

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Acknowledgements

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